SHEEL I OF I											
INFO	CIT	ΥA	ON DISCLOSTION IN AN	SURE	ATTY. DOCKET NO. 63979-032		SERIAL NO. 10/643,944				
VOILE!	X^{Ai}	'PL	LICATION								
APR 2 0 2004 CS					APPLICANT Yoshiaki HASEGAWA, et al.						
MAK 5	3	ma	10 1440		SII ING DATE	FILING DATE GROUP					
(PTO-1449)									2828		
E TRADE				U.S. PATEN	NT DOCUMENTS						
EXAMINER'S			Document Number	Publication Dat	a Name of Patentee or Appli	Name of Patentee or Applicant of Cited Pages, Columns, Lines, Where					
INITIALS	CITE NO.	Num	ber-Kind Codez (7 known)	MM-DD-YYYY					Relevant Passages or Relevant Figures Appear		
M		US	5,345,483	5,345,463 09/06/1994 Mannoh et al.							
		US		·····							
		US									
		บร									
		US					<u> </u>				
FOREIGN PATENT DOCUMENTS											
EXAMINER'S INITIALS	CITE NO.	Foreign Patent Document Country Codes -Number 4 -Kind Codes (if known)		Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines Where Relevant Figures Appear			Translation		
								Yes	No		
W	\	JP 10-200214 A JP 6-283825 A		07/31/1998	NEC CORP				х.		
2N	-	_	JP 6-283825 A JP 4-275479 A	10/07/1994	TOYODA GOSEI CO., LTD. NEC CORP.	ii			X		
24)	\-		JP 2000-21789	01/21/2000	TOSHIBA CORP.	\			-		
\$1°	- \		JP 5-291686	11/05/1993	TOSTIBA CORF.	 			×		
Cut	\	 	JP 11-251687 -	09/17/1999	 •	-	$\overline{}$		X		
OTHER ART (including Author, Title, Date, Perlinent Pages, Etc.)											
EXAMINER'S INITIALS	CITE NO. Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.										
ar.	1	GOTO, S., et al. " InGaN: Improvement of quantum efficiency by InGaN Interlayer for blue-violet laser diodes." Sony Shiroishi Semiconductor Inc. 28p-E-12, Page 369									
CW		NAKAMURA, Shuji. "InGaN Multiquantum-Well-Structure Laser Diodes with GaN-AlGaN Modulation –Doped Strained-Layer Superlattices." IEEE Journal of Selected Topics in Quantum Electronics, Vol. 4, No.3, May/June 1998, pp. 483-489									
LW.		KNEISSL, Michael., et al. " Performance and degradation of continuous-wave InGaN multiple-quantum-well laser diodes on epitaxially laterally overgrown GaN substrates." Applied Physics Letters, Volume 77, Number 13, September 25, 2000, pp. 1931-1933									
SVNV		NAKAMURA, Shuji., et al. " UV/Blue/Green InGaN-Based LEDs and Laser Diodes Grown on Epitaxially Laterally Overgrown GaN." IEICE Trans. Electron., Vol E83-C, No. 4, April 2000, pp. 529-535							У		
Khy.		ΤΟ	TOJYO, Tsuyoshi., et al. "GaN-Based High Power Blue-Violet Laser Diodes." The Japan Society for Applied Physics, Volume 40, Part 1. No. 5A, May 2001, pp.3208-3210								
Cu			KURODA, Naotaka., et al. " Precise control of pn-junction profiles for GaN-based LD structures using GaN substrates with low distocation densities." Journal of Crystal Growth 189/190 (1998) pp. 551-555								
M		OHBA, Y., et al" A study on strong memory effects for Mg doping GaN metalorganic chemical vapor deposition." Journal of Crystal growth 145 (1994) pp. 214-218							."		
Ku)		BLAAUW, C., et al. " Secondary Ion mass spectrometry and electrical characterization of Zn diffusion in n-type InP." J. Appl. Phys. 66(2), July 15, 1989, American Institute of Physics, pp. 605610									
EXAMINER DATE CONSIDERED											
Harries !					5/ 25	5/25/05					

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

1 Applicant's unique citation designation number (optional). 2 Applicant is to place a check mark here if English language Translation is attached.